

TIP31C

Power transistors

General features

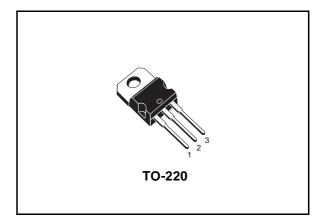
- New enhanced series
- High switching speed
- h_{FE} improved linearity
- h_{FE} Grouping

Applications

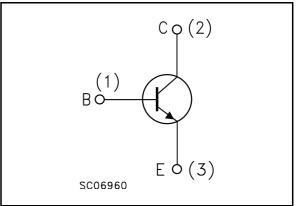
■ Linear and switching industrial application

Description

The TIP31C is a base island technology NPN power transistor in TO-220 plastic package with better performances than the industry standard TIP31C that make this device suitable for audio, power linear and switching applications. The PNP type is TIP32C.



Internal schematic diagram



Order codes

Part Number	Marking	Package	Packing
TIP31C Note: on page 4	TIP31C R TIP31C O TIP31C Y	TO-220	Tube

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1 Absolute maximim ratings

Table 1.	Absolute maximim ratings

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-base voltage (I _E = 0)	100	V
V _{CEO}	Collector-emitter voltage ($I_B = 0$)	100	V
V _{EBO}	Emitter-base voltage (I _C = 0)	5	V
۱ _C	Collector current	3	А
I _{CM}	Collector peak current	5	А
Ι _Β	Base current	1	А
P _{TOT}	Total dissipation at $T_{case} = 25^{\circ}C$ Total dissipation at $T_{amb} = 25^{\circ}C$	40 2	W W
T _{stg}	Storage temperature	-65 to 150	°C
Τ _J	Max. operating junction temperature	150	°C

2 Electrical characteristics

 $(T_{case} = 25^{\circ}C \text{ unless otherwise specified})$

Parameter	Test cor	nditions	Min.	Тур.	Max.	Unit
Collector cut-off current (I _B = 0)	V _{CE} = 60V				0.3	mA
Emitter cut-off current ($I_C = 0$)	$V_{EB} = 5V$				1	mA
Collector cut-off current (V _{BE} = 0)	V _{CE} = 100V				0.2	mA
Collector-emitter sustaining voltage (I _B = 0)	I _C = 30mA		100			V
Collector-emitter saturation voltage	I _C = 3A	I _B = 375mA			1.2	V
Base-emitter voltage	I _C = 3A	$V_{CE} = 4V$			1.8	V
DC current gain	-		25 10 20 40		24 44 50	
	ParameterCollector cut-off current $(I_B = 0)$ Emitter cut-off current ($I_C = 0$)Collector cut-off current $(V_{BE} = 0)$ Collector-emittersustaining voltage ($I_B = 0$)Collector-emitter saturationvoltageBase-emitter voltage	ParameterTest corCollector cut-off current ($I_B = 0$) $V_{CE} = 60V$ Emitter cut-off current ($I_C = 0$) $V_{EB} = 5V$ Collector cut-off current ($V_{CE} = 100V$ $V_{CE} = 100V$ Collector-emitter sustaining voltage ($I_B = 0$) $I_C = 30mA$ Collector-emitter saturation voltage $I_C = 3A$ Base-emitter voltage $I_C = 3A$ DC current gain $I_C = 3A$ Group R Group O $Group R$	ParameterTest conditionsCollector cut-off current ($I_B = 0$) $V_{CE} = 60V$ Emitter cut-off current ($I_C = 0$) $V_{EB} = 5V$ Collector cut-off current ($V_{BE} = 0$) $V_{CE} = 100V$ Collector-emitter sustaining voltage ($I_B = 0$) $I_C = 30mA$ Collector-emitter saturation voltage $I_C = 3A$ $I_B = 375mA$ Base-emitter voltage $I_C = 3A$ $V_{CE} = 4V$ DC current gain $I_C = 1A$ $V_{CE} = 4V$ Group R Group O $Group R$ $Group R$	ParameterTest conditionsMin.Collector cut-off current ($I_B = 0$) $V_{CE} = 60V$ Emitter cut-off current ($I_C = 0$) $V_{EB} = 5V$ Collector cut-off current ($V_{BE} = 0$) $V_{CE} = 100V$ Collector-emitter sustaining voltage ($I_B = 0$) $I_C = 30mA$ 100Collector-emitter saturation voltage $I_C = 3A$ $I_B = 375mA$ Base-emitter voltage $I_C = 3A$ $V_{CE} = 4V$ DC current gain $I_C = 3A$ $V_{CE} = 4V$ DC current gain $I_C = 3A$ $V_{CE} = 4V$	ParameterTest conditionsMin.Typ.Collector cut-off current ($I_B = 0$) $V_{CE} = 60V$ Emitter cut-off current ($I_C = 0$) $V_{EB} = 5V$ Collector cut-off current ($V_{BE} = 0$) $V_{CE} = 100V$ Collector-emitter sustaining voltage ($I_B = 0$) $I_C = 30mA$ 100Collector-emitter saturation voltage $I_C = 3A$ $I_B = 375mA$ Base-emitter voltage $I_C = 3A$ $V_{CE} = 4V$ DC current gain $I_C = 3A$ $V_{CE} = 4V$ 25DC current gain $Group R$ 10	ParameterTest conditionsMin.Typ.Max.Collector cut-off current ($I_B = 0$) $V_{CE} = 60V$ 0.30.3Emitter cut-off current ($I_C = 0$) $V_{EB} = 5V$ 11Collector cut-off current ($V_{BE} = 0$) $V_{CE} = 100V$ 0.20.2Collector-emitter sustaining voltage ($I_B = 0$) $I_C = 30mA$ 1001.2Collector-emitter saturation voltage $I_C = 3A$ $I_B = 375mA$ 1.2Base-emitter voltage $I_C = 3A$ $V_{CE} = 4V$ 1.8DC current gain $I_C = 1A$ Group R Group Q2044

	Table 2.	Electrical	characteristics
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1. Pulsed duration = 300 ms, duty cycle $\ge 1.5\%$

Note: Product is pre-selected in DC current gain (Group R, Group O and Group Y). STMicroelectronics reserves the right to ship each groups according to production availability. Please contact your nearest STMicroelectronics sales office for delivery details.

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I_{S/B}

2.1 Electrical characteristics (curve)

Figure 1. Safe Operating area

Figure 2. Derating curves

%

100

50

0

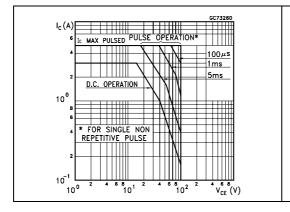


Figure 3. DC-current gain

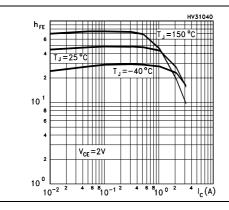
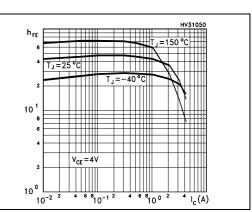


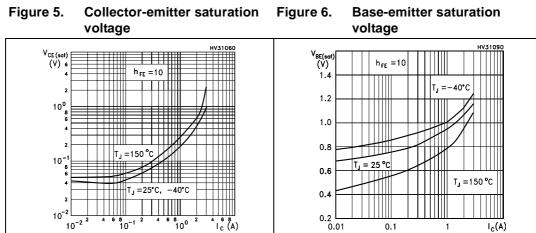
Figure 4. DC-current gain

50



P_{tot}

100



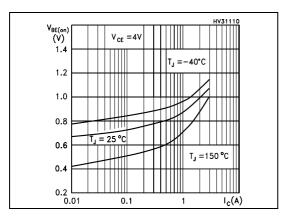


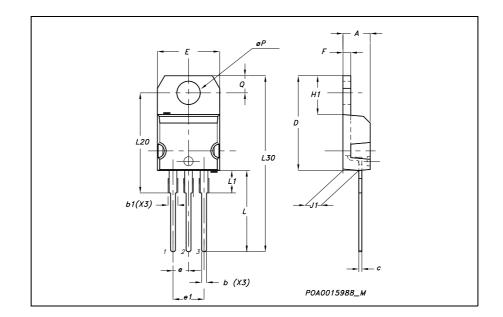
Figure 7. Base-emitter on voltage

3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com



		mm.		inch		
DIM.	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX
А	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
C	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
е	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	





4 Revision history

Table 3. Revision history

Date	Revision	Changes
20-Apr-2006	1	New release



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